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TITLE: MANUFACTURE OF THIN FILM TRANSISTOR

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ABSTRACT:

PURPOSE: To reduce operating time and costs by removing
n<SP>+</SP> a-Si and
a-Si layers located at a display section through a dry
process using source and
drain electrodes as masks.

CONSTITUTION: A gate electrode 12 is formed on a
transparent insulating
substrate 11, and gate insulating film 13, a-Si layer 14,
n<SP>+</SP>a-Si layer
14' and a single-or double-layered metal film (electrode
material) are formed
in the form of films on the gate electrode 12.

Subsequently, source and drain electrodes 15 and 16 are patterned using a photolithographic technique, and n<SP>+</SP>a-Si layer 14' and a-Si layer 14 located at an indication part are removed by a dry process using the electrodes 15 and 16 as masks. After that, display electrode 17, source electrode 15 and drain electrode 16 are formed and the n<SP>+</SP>a-Si layer 14' exposed at a channel part is removed by a dry process to form a surface protecting film 18. Thus, a thin film transistor 19 is obtained.

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